

HD74LV2GT00A

Dual 2-input NAND Gates

HITACHI

ADE-205-662 (Z)

Rev.0
Jan. 2002

Description

The HD74LV2GT00A has dual two-input NAND gates in a 8 pin package. Low voltage and high speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

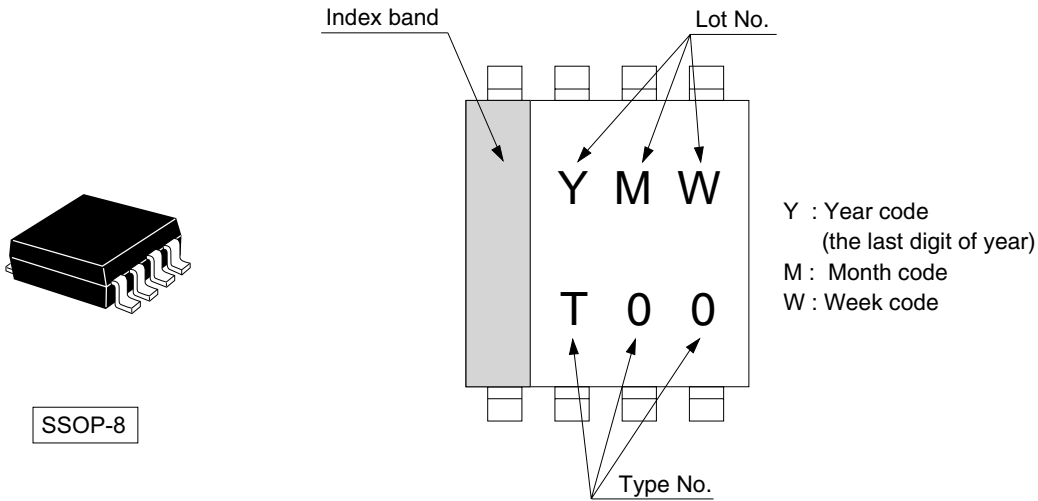
Features

- The basic gate function is lined up as hitachi uni logic series.
- Supplied on emboss taping for high speed automatic mounting.
- TTL compatible input level.
Supply voltage range : 4.5 to 5.5 V
Operating temperature range : -40 to +85°C
- All inputs V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V)
All outputs V_o (Max.) = 5.5 V (@ V_{CC} = 0 V)
- Output current ± 12 mA (@ V_{CC} = 4.5 V to 5.5 V)
- All the logical input has hysteresis voltage for the slow transition.
- Package type

Package type	Package code	Package suffix	Taping code
SSOP-8 pin	TTP-8DB	US	E (3,000 pcs / Reel)

Outline and Article Indication

- HD74LV2GT00A



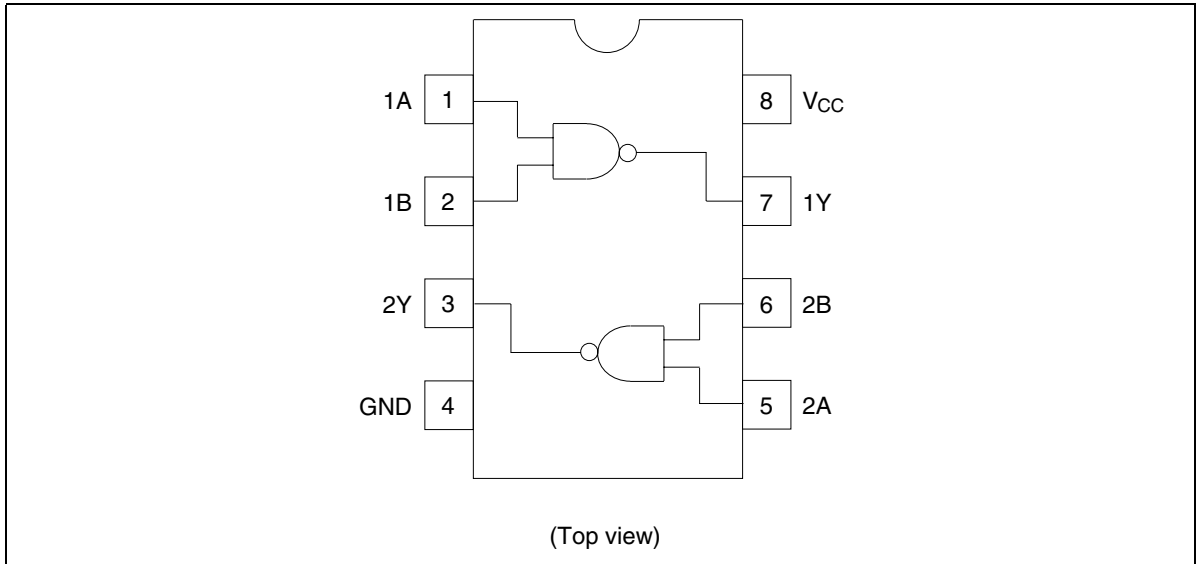
Function Table

Inputs		Output Y
A	B	
L	L	H
L	H	H
H	L	H
H	H	L

H : High level

L : Low level

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V_{CC}	-0.5 to 7.0	V	
Input voltage range ^{*1}	V_I	-0.5 to 7.0	V	
Output voltage range ^{*1,2}	V_O	-0.5 to $V_{CC} + 0.5$ -0.5 to 7.0	V	Output : H or L V_{CC} : OFF
Input clamp current	I_{IK}	-20	mA	$V_I < 0$
Output clamp current	I_{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I_O	±25	mA	$V_O = 0$ to V_{CC}
Continuous current through V_{CC} or GND	I_{CC} or I_{GND}	±50	mA	
Maximum power dissipation at $T_a = 25^{\circ}\text{C}$ (in still air) ^{*3}	P_T	200	mW	
Storage temperature	T_{stg}	-65 to 150	°C	

- Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore no two of which may be realized at the same time.
1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 2. This value is limited to 5.5 V maximum.
 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit
Supply voltage	V_{CC}	4.5 to 5.5	V
Input voltage	V_{IN}	0 to 5.5	V
Output voltage	V_{OUT}	0 to V_{CC}	V
Operating temperature	T_{opr}	-40 to +85	°C
Input rise / fall time	t_r, t_f	0 to 20 ($V_{CC} = 4.5$ to 5.5 V)	ns

Electrical Characteristic

- $T_a = -40$ to 85°C

Item	Symbol	V_{cc} (V) *	Min	Typ	Max	Unit	Test condition
Input voltage	V_{IH}	4.5 to 5.5	2.0	—	—	V	
	V_{IL}	4.5 to 5.5	—	—	0.8		
Hysteresis voltage	V_H	5.0	—	0.15	—	V	$V_T^+ - V_T^-$
Output voltage	V_{OH}	Min to Max	$V_{CC}-0.1$	—	—	V	$I_{OH} = -50\ \mu\text{A}$
		4.5	3.8	—	—		$I_{OH} = -12\ \text{mA}$
	V_{OL}	Min to Max	—	—	0.1		$I_{OL} = 50\ \mu\text{A}$
		4.5	—	—	0.55		$I_{OL} = 12\ \text{mA}$
Input current	I_{IN}	0 to 5.5	—	—	± 1	μA	$V_{IN} = 5.5\ \text{V}$ or GND
Quiescent supply current	I_{CC}	5.5	—	—	10	μA	$V_{IN} = V_{CC}$ or GND, $I_O = 0$
	ΔI_{CC}	5.5	—	—	1.5	mA	One input $V_{IN} = 3.4\ \text{V}$, other input V_{CC} or GND
Output leakage current	I_{OFF}	0	—	—	5	μA	$V_O = 5.5\ \text{V}$
Input capacitance	C_{IN}	5.0	—	2.5	—	pF	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

- $V_{CC} = 5.0 \pm 0.5 \text{ V}$

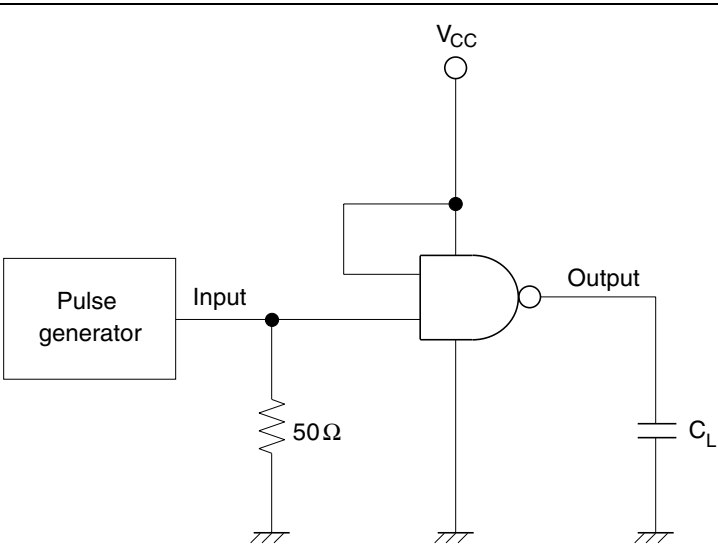
Item	Symbol	Ta = 25°C			Ta = -40 to 85°C		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max	Min	Max				
Propagation delay time	t_{PLH}	—	5.0	6.9	1.0	8.0	ns	$C_L = 15 \text{ pF}$	A or B	Y
	t_{PHL}	—	5.5	7.9	1.0	9.0		$C_L = 50 \text{ pF}$		

Operating Characteristics

- $C_L = 50 \text{ pF}$

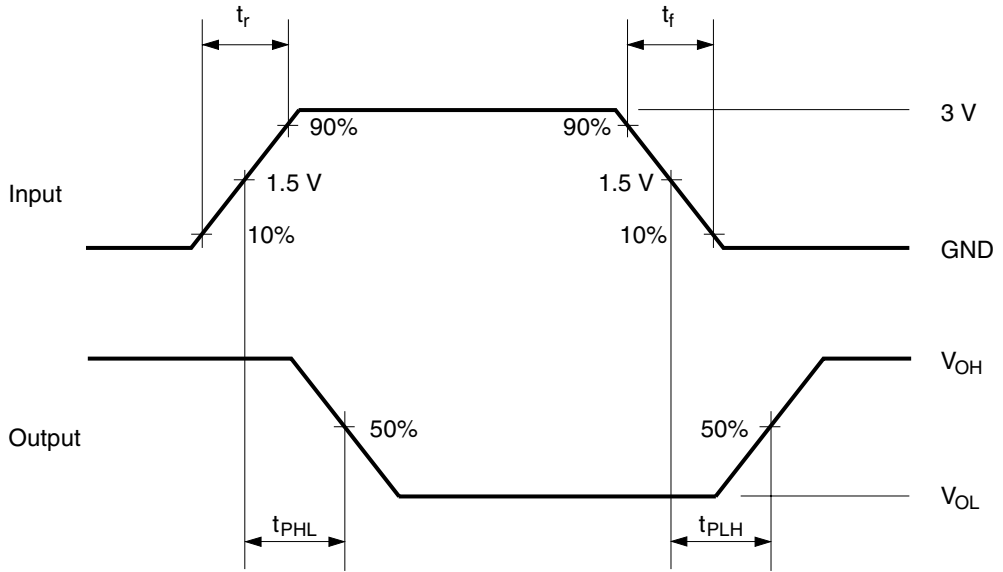
Item	Symbol	$V_{CC} \text{ (V)}$	Ta = 25°C			Unit	Test Conditions
			Min	Typ	Max		
Power dissipation capacitance	C_{PD}	5.0	—	11.0	—	pF	f = 10 MHz

Test Circuit



Note: Operating current test time, output is open.

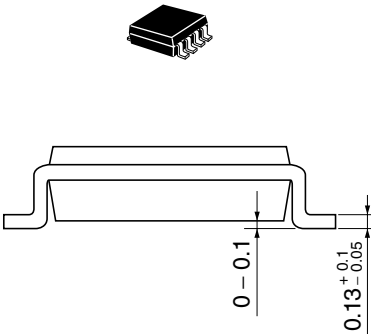
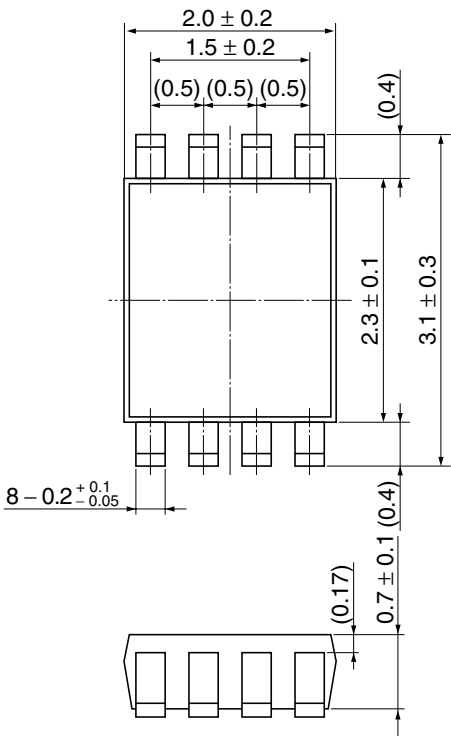
• Waveforms



- Notes: 1. Input waveform : $PRR \leq 1 \text{ MHz}$, $Z_o = 50 \Omega$, $t_r \leq 3 \text{ ns}$, $t_f \leq 3 \text{ ns}$.
 2. The output are measured one at a time with one transition per measurement.

Package Dimensions

As of July, 2001
Unit: mm



Hitachi Code	TTP-8DB
JEDEC	—
JEITA	—
Mass (reference value)	0.010 g

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Sales offices

HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: (03) 3270-2111 Fax: (03) 3270-5109

URL <http://www.hitachisemiconductor.com/>

For further information write to:

Hitachi Semiconductor (America) Inc.
179 East Tasman Drive
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe Ltd.
Electronic Components Group
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585200

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen
Postfach 201, D-85619 Feldkirchen
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://semiconductor.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road
Hung-Kuo Building
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://semiconductor.hitachi.com.hk>

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